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**MICRON ANNOUNCES SAMPLE AVAILABILITY FOR ITS  
THIRD-GENERATION RLD RAM<sup>®</sup> MEMORY**

*Company Introduces Integrated Silicon Solution, Inc. as Second Source Partner*

**BOISE, Idaho, May 26, 2011** – Micron Technology, Inc. today announced that early engineering samples are available for its third-generation reduced latency DRAM (RLDRAM 3 memory). RLD RAM 3 is a high-bandwidth memory technology that enables a more efficient transfer of information across the network. Designed for high-performance networking applications, including high-end routers and switches that require back-to-back READ/WRITE operations or completely random access, RLD RAM 3 memory is an ideal choice for 40 Gigabit Ethernet (GbE) and 100 GbE designs, packet buffering and inspection, and lookup tables. Additionally, RLD RAM 3 memory offers significant improvements in speed, density, latency and power consumption.

The proliferation of Internet-based video services like IPTV and video on demand, combined with growth in mobile applications and cloud computing, is driving the need for a more efficient network infrastructure that can keep pace with the amount of data being moved online. RLD RAM 3 memory provides networking customers with a high-bandwidth, low-latency solution that can support the increases in protocol operating speeds, such as 100 GbE.

RLDRAM 3 memory provides sustainable data rates up to 2133 megabits per second (Mb/s) and offers the industry's lowest random access latency of sub-10 nanoseconds. It also offers greater energy efficiency through familiar 1.2V IO and 1.35V core voltage levels.

“At Micron, we recognize the pressure customers face today to optimize their network technology to support the growth in data volume and deal with the associated complexity of the changing infrastructure,” said Bruce Franklin, Director of Networking and Storage Business Development for Micron’s DRAM Solutions Group. “RLDRAM 3 memory is a low-latency,

high-bandwidth solution that provides plenty of headroom to accommodate our customers' evolving networking memory requirements.”

Micron today also announced that Integrated Silicon Solution, Inc. (ISSI) will become an alternate supplier of Micron's RLD RAM 3 memory, providing assurance of commercial volume and longevity for networking customers.

“By working closely with Micron, we will be able to support our customers' requests to provide RLD RAM 3 memory,” said Pat Lasserre, ISSI Director of Strategic Marketing. “With the addition of RLD RAM 3 to our product line, we are excited to address customers' demands for long-term support of specialized, high-performance memory technologies, driven by networking standards like 100 GbE.”

### **Product Availability**

Information on ordering RLD RAM 3 product samples can be found on our [Web site](#). Micron is expected to begin production of RLD RAM 3 memory during the second half of 2011.

### **Relevant Links**

There are other ways to stay up-to-date on Micron and Crucial news:

- Micron Innovations Blog: [www.micronblogs.com](http://www.micronblogs.com)
- Micron on Twitter: <http://twitter.com/microntechnews> and <http://twitter.com/realssd>
- Micron Pressroom: [www.micron.com/media](http://www.micron.com/media)

### **About Micron**

Micron Technology, Inc., is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets a full range of DRAM, NAND and NOR flash memory, as well as other innovative memory technologies, packaging solutions and semiconductor systems for use in leading-edge computing, consumer, networking, embedded and mobile products. Micron's common stock is traded on the NASDAQ under the MU symbol. To learn more about Micron Technology, Inc., visit [www.micron.com](http://www.micron.com).

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*This press release contains forward-looking statements regarding production of RLDRAM 3. Actual events or results may differ materially from those contained in the forward-looking statements. Please refer to the documents Micron files on a consolidated basis from time to time with the Securities and Exchange Commission, specifically Micron's most recent Form 10-K and Form 10-Q. These documents contain and identify important factors that could cause the actual results for Micron on a consolidated basis to differ materially from those contained in our forward-looking statements (see Certain Factors). Although we believe that the expectations reflected in the forward-looking statements are reasonable, we cannot guarantee future results, levels of activity, performance or achievements.*